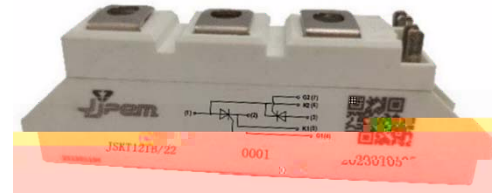


JSKT121B/22

Description

- 1) A package of series of two chips.
- 2) With high thermal conductivity DBC as the insulation.
- 3) Welding by vacuum welding technology, which provide high reliability.



Typical Application

Storage temperature range		T_{stg}	-40-125	
Repetitive peak off-state voltage	$T_j=25$	V_{DRM}	2200	V
Repetitive peak reverse voltage	$T_j=25$	V_{RRM}	2200	V
Non-repetitive peak off-state voltage	$T_j=25$	V_{DSM}	2300	V
Non-repetitive peak reverse voltage	$T_j=25$	V_{RSM}	2300	V
Average on-state current	$T_C=85$	$I_{T(AV)}$		
Peak on-state surge current	$t_p=10ms V_R=0.6V_{RRM}$	I_{TSM}	2700	A
I^2t value for fusing	$t_p=10ms V_R=0.6V_{RRM}$	I^2t	36500	A ² s

Critical rate of rise of on-state current

I

Unit

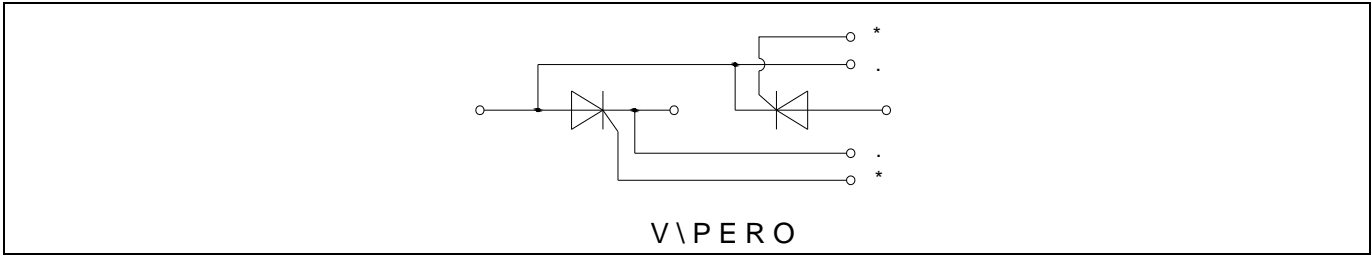
Peak on-state voltage	$I_T=360A t_p=380\mu s$	V_{TM}	1.8	V
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Threshold voltage

	$D=V_{DRM}$			
	$T_C=25$	I_{DRM1}	100	μA
	$T_C=125$	I_{DRM2}	40	mA



Repetitive peak reverse current	$V_R = V_{RRM}$			
	$T_C = 25$	I_{RRM1}	100	μA
	$T_C = 125$	I_{RRM2}	40	mA



,QVWUXFWLRQV DQG 3UHFDXWLRQV

7KHUH LV QR VHYHUH YLEUDWLRQ DQG VKRFN LQ RSHUDWLQJ HQY



FIG.3:Forward characteristics
(per thyristor)

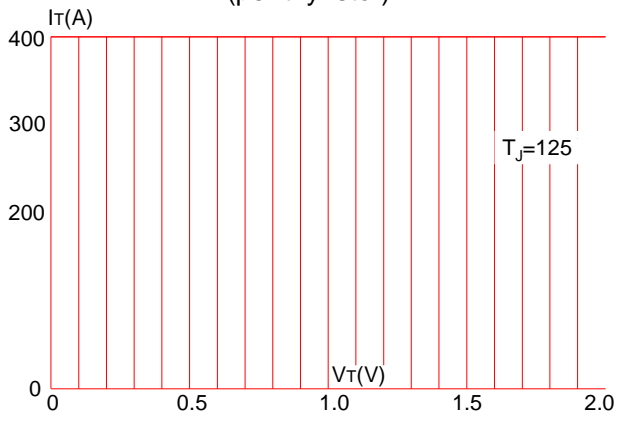


FIG.4: Relative variations of gate trigger current, holding